

# Verification and Extraction of 3D Stack Component Interactions



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# Outline

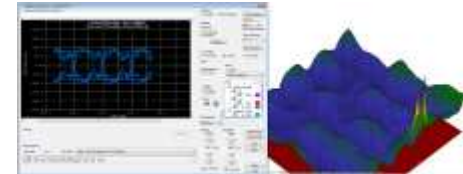
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- EDA Challenges in 3D Stack Modeling and Design
  - Different phenomena: electrical, thermal , mechanical
  - Cross- domain integration
- 3D Stack Verification and Extraction
  - Stack verification flow
  - Extraction solutions
- Intra Die Component Interactions and Extraction
  - TSV to TSV
  - TSV to RDL
- Inter Die Interactions
  - Various bonding schemes
  - Analysis of die-to-die capacitive coupling impact
  - In context extraction

# EDA Challenges in Modeling and Design of 3D Stacks

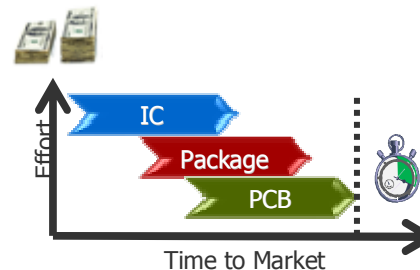
## ■ Modeling

- Different phenomena: electrical, thermal, mechanicals;
- Interaction modeling
- Tradeoff between needed accuracy and model complexity and flow integration
- Consistency between different levels of abstraction

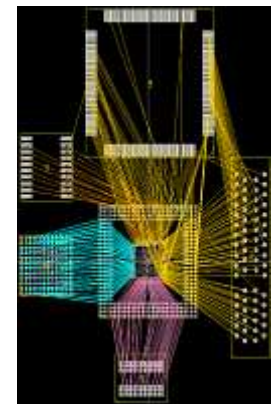


## ■ Design

- Design exploration/optimization tools, managing interactions and controlling parametric yield
- Cross-domain integration
  - ICs, Interposer, Package, Board



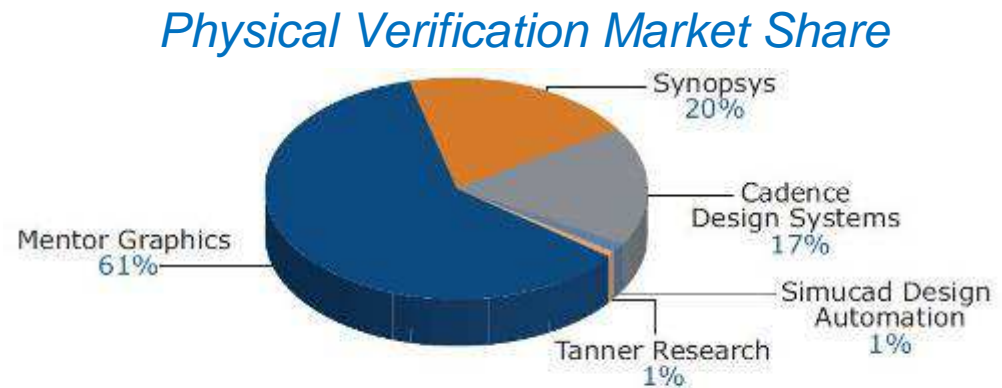
- Work on resolving issues related to multiple disconnected tools with no standard methodology/flow to synchronize and transfer design data between design disciplines and abstraction levels



- Standards needed for tool interfaces and data exchange format

# Expanding Calibre to the 3DIC Domain

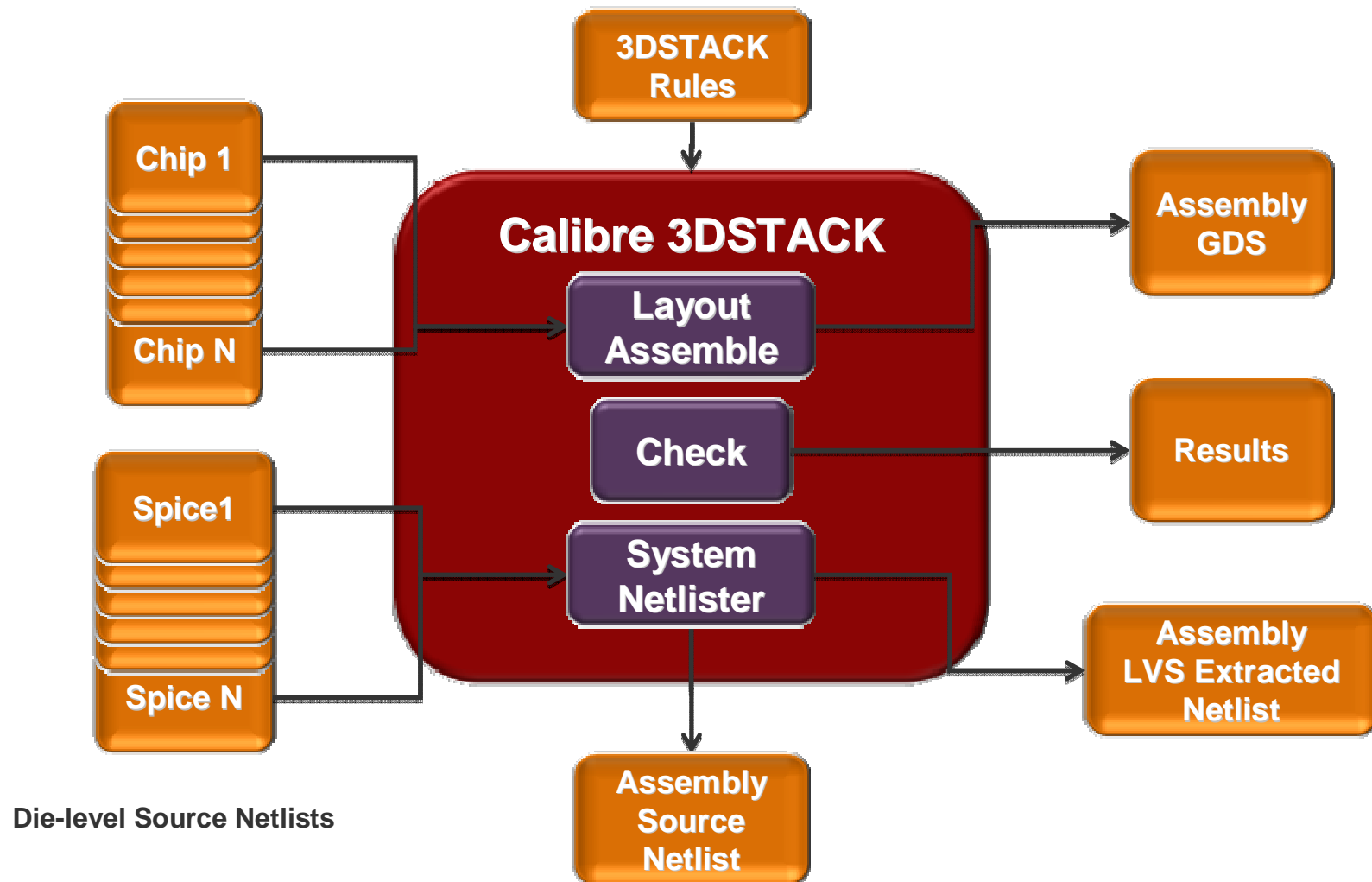
- Calibre is the dominant sign-off tool for leading IDM, memory, fabless and foundries
  - Lowest Risk
  - Fastest Performance



*(Source: Gary Smith EDA, November 2013)*

- Expanding Calibre for 3DIC Verification & Analysis
  - Physical Verification
  - Parasitic Extraction
  - Thermal Analysis
  - Stress Analysis

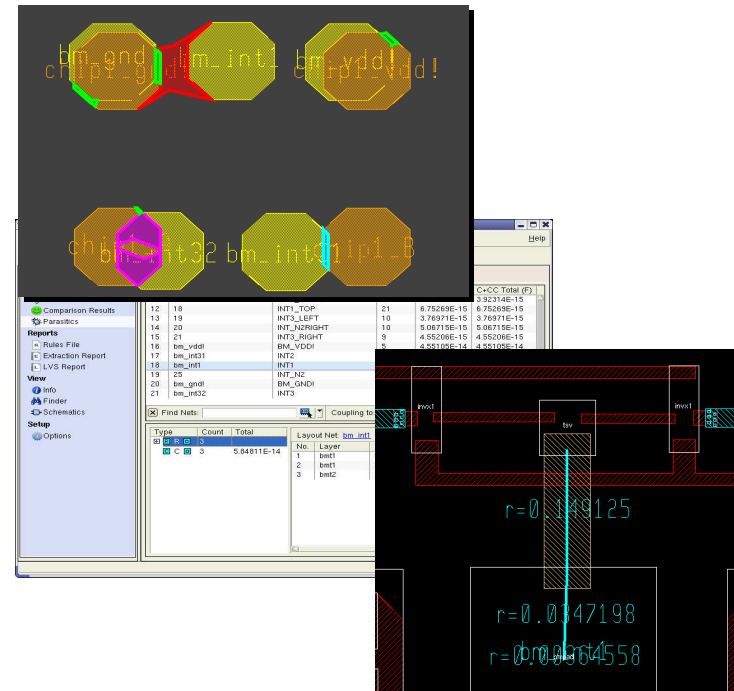
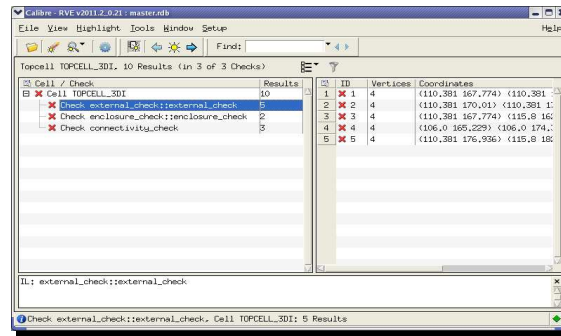
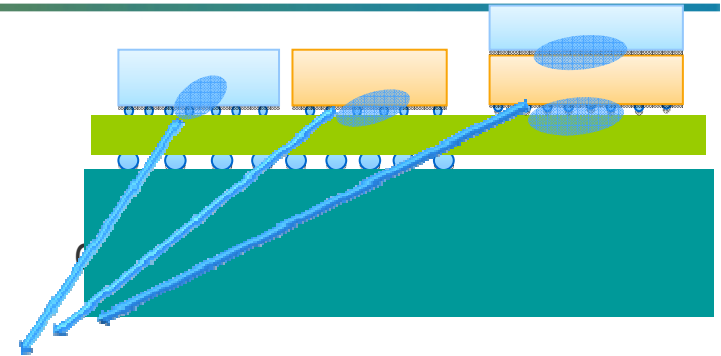
# Calibre 3DSTACK: Verification Flow



# MG Stack Verification Flow

## Calibre 3DSTACK

- Verify with micro-bumps are physically aligned
- Verify proper electrical connectivity through interfaces



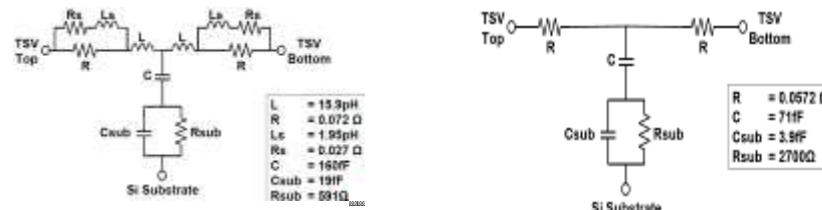
## Calibre xRC/xACT3D

- Extract parasitics of the Dies and Interposer interconnect
- Insert provided TSV circuit into integrated parasitics/TSV netlists, or extract TSV

# Extraction solutions: TSV Modeling Approaches

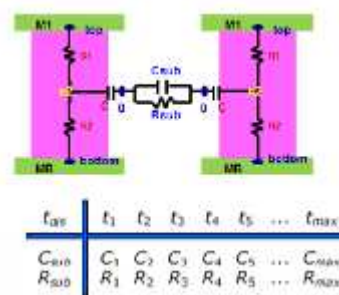
## ■ Stand Alone TSV models

- Advantage: Easy to integrate into a flow ; Sufficient in many situations
- Challenges: Not adequate for high density, high frequency applications

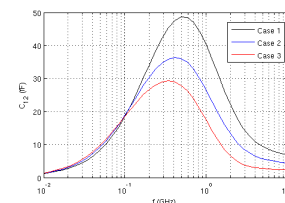
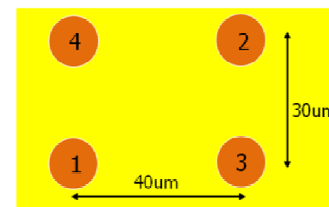


## ■ Compact parametrized models

- Advantage: Can account for some interactions; Faster than FS
- Challenges :Hard to account for all situations, to parameterize for all important variables



- Case 1: TSV 3 and TSV 4 are not present in layout
- Case 2: TSV 4 is not present in layout
- Case 3: All 4 of the TSV's are present



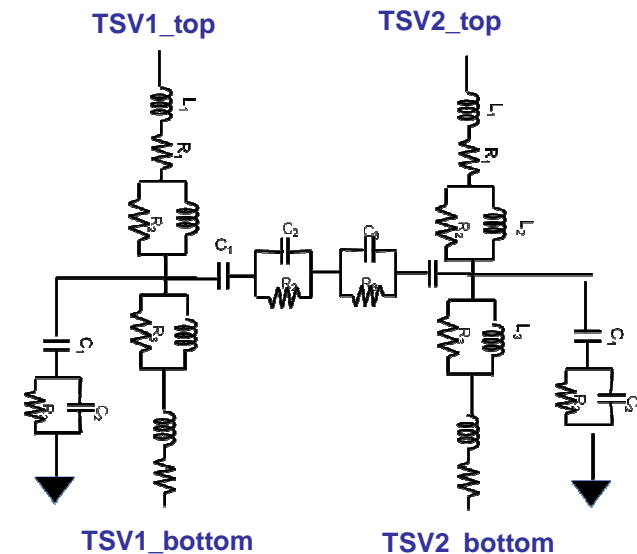
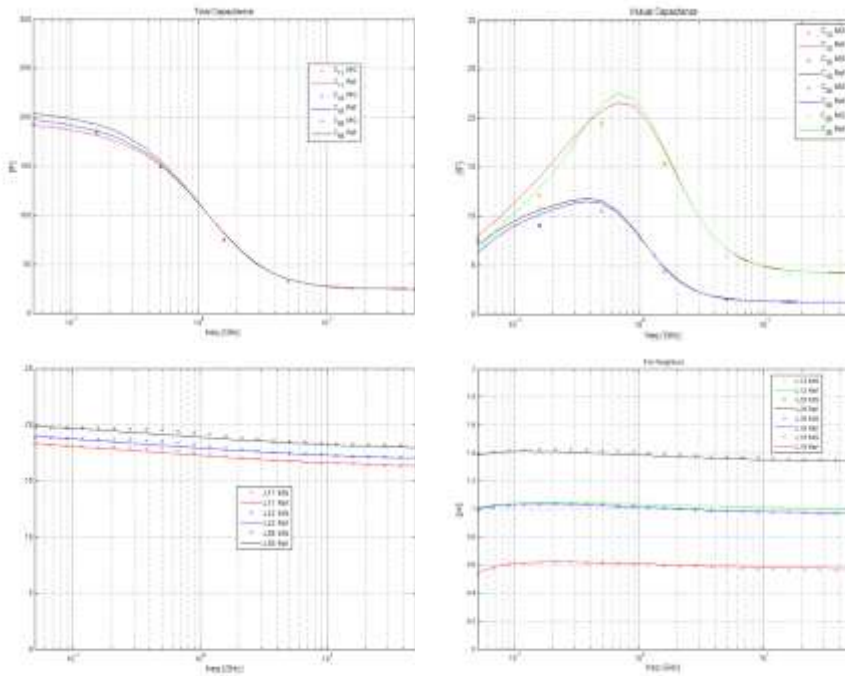
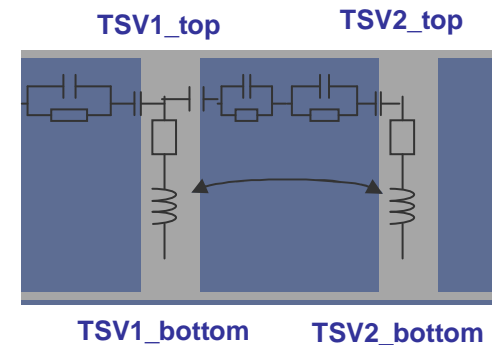
## ■ Field solver approach

- Advantage: Most accurate
- Challenges: Performance; Integration

# Fast Field Solver Based Solution

- Fast-Field Solver based solution extracts TSV parasitics and TSV to TSV couplings (capacitive and inductive)

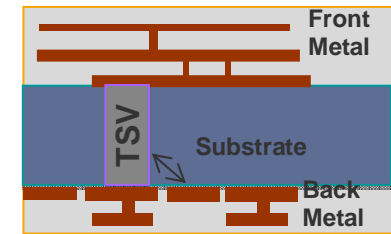
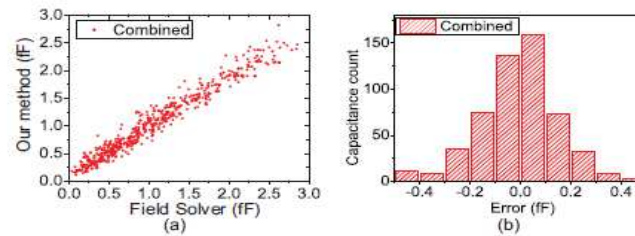
- Produces netlist consisting of frequency-independent linear elements.
- Accurate vs. reference results
- Order of magnitude faster than other field solvers





# Extraction of TSV to Interconnect coupling

- Model and extract TSV to interconnect extraction
- Full chip solution within 2% accuracy vs FS



- Significant impact:

TABLE I  
TSV-TO-WIRE COUPLING FULL-CHIP IMPACT.

Is TSV-to-wire included?	no	yes
Longest path delay (ns)	4.48	5.08 (+13.4%)
Total power on TSV net (mW)	0.303	0.356 (+17.6%)
Total net switching power (mW)	2.42	2.50 (+3.3%)
Total noise on TSV net (V)	32.5	78.2 (+104%)

- To Reduce the impact

Table 6: Keep-out-zone impact on full-chip design. Power is reported in mW.

KOZ size ( $\mu m$ )	0.5	2.5	5
Longest path delay (ns)	5.08	4.95 (-2.6%)	4.77 (-6.1%)
Total power on TSV net	0.356	0.342 (-3.9%)	0.327 (-8.1%)
Total net switching power	2.50	2.47 (-1.2%)	2.45 (-2.0%)
Total noise on TSV net (V)	78.2	67.0 (-14.3%)	42.9 (-45.1%)

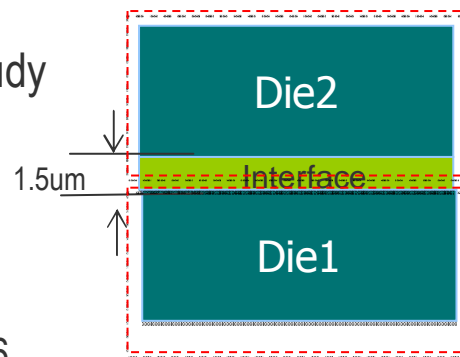
Table 7: Guard ring impact on full-chip design with 2.5 $\mu m$  KOZ. Power is reported in mW.

Guard ring width ( $\mu m$ )	0	0.5	1.5
Longest path delay (ns)	4.95	4.98 (+0.6%)	5.01 (-1.2%)
Total power on TSV net	0.342	0.351 (+2.6%)	0.358 (+4.7%)
Total net switching power	2.47	2.475 (+0.2%)	2.479 (+0.4%)
Total noise on TSV net (V)	67.0	58.0 (-13.4%)	53.6 (-20.0%)

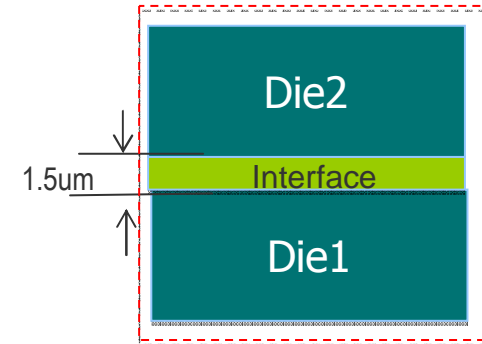


# Inter die parasitic extraction in F2F bonding

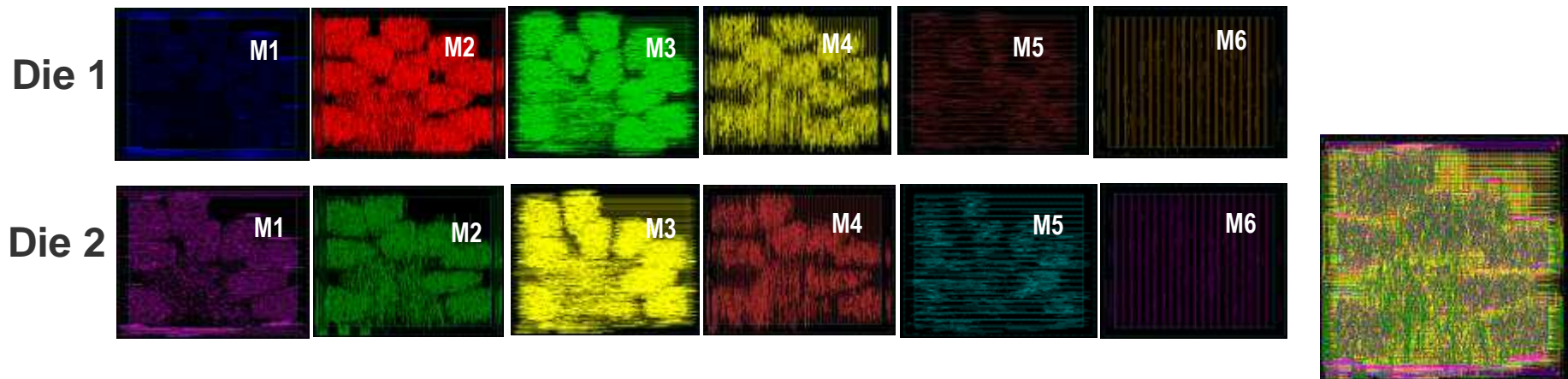
- Two different scenarios for LVS/PEX to study impact of die-to die coupling capacitance
- Dies are connected F2F
- Each die has 6 metal layers
- w/s varies from 0.05/0.05u for M1 to 0.36/0.36 (M5) and 1.8/1.8u (M6 )
- Distance between the dies varied from 10u-1u



Individual die LVS/PEX  
Parasitics extracted separately  
Ignoring intra-die coupling

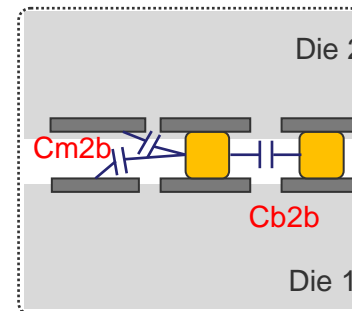
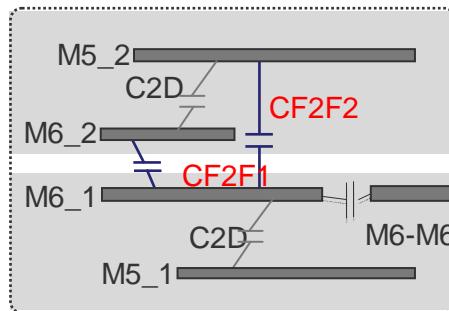


3D stack LVS/PEX  
Extracting interface and  
die coupling parasitics



# Impact of die capacitive coupling

## Impact on various capacitance components



- Impact of charge sharing on top metal coupling capacitance in the same die (M6-M6):  
overestimated by >50% when the dies get close to 1 micron
- No impact (<1%) on lower layer capacitances M5-M5
- Die to die coupling (CF2F1, CF2F2) becomes comparable to intra die coupling (M6-M6)

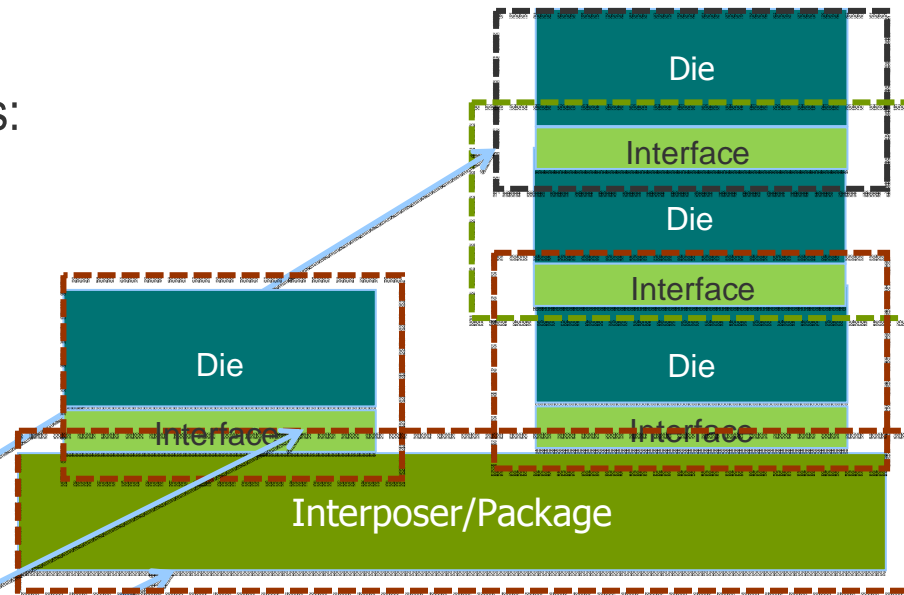
## Impact on full chip noise and critical path delay

- Significant delay impact on individual nets 10%-20% , depending on the design type
- Significant impact on noise voltage , up to 80%
- No impact on power

# In Context Calibration/Extraction

Inter die and die to interposer interactions:

- Interface extraction
- Capacitive coupling



Describe geometry and materials for inter-die region

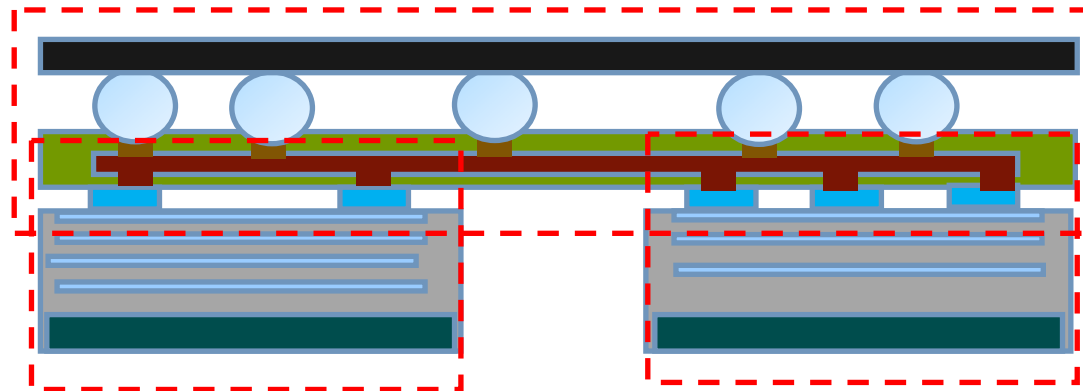
- Die -to die
- Die -to- interposer
- Die(or interposer) to package

- Each die would be calibrated/extracted in-context
- Coupling capacitances would be folded in the victim die parasitics
- Interfaces will be owned by the specified dies

# InFO WLP extraction example

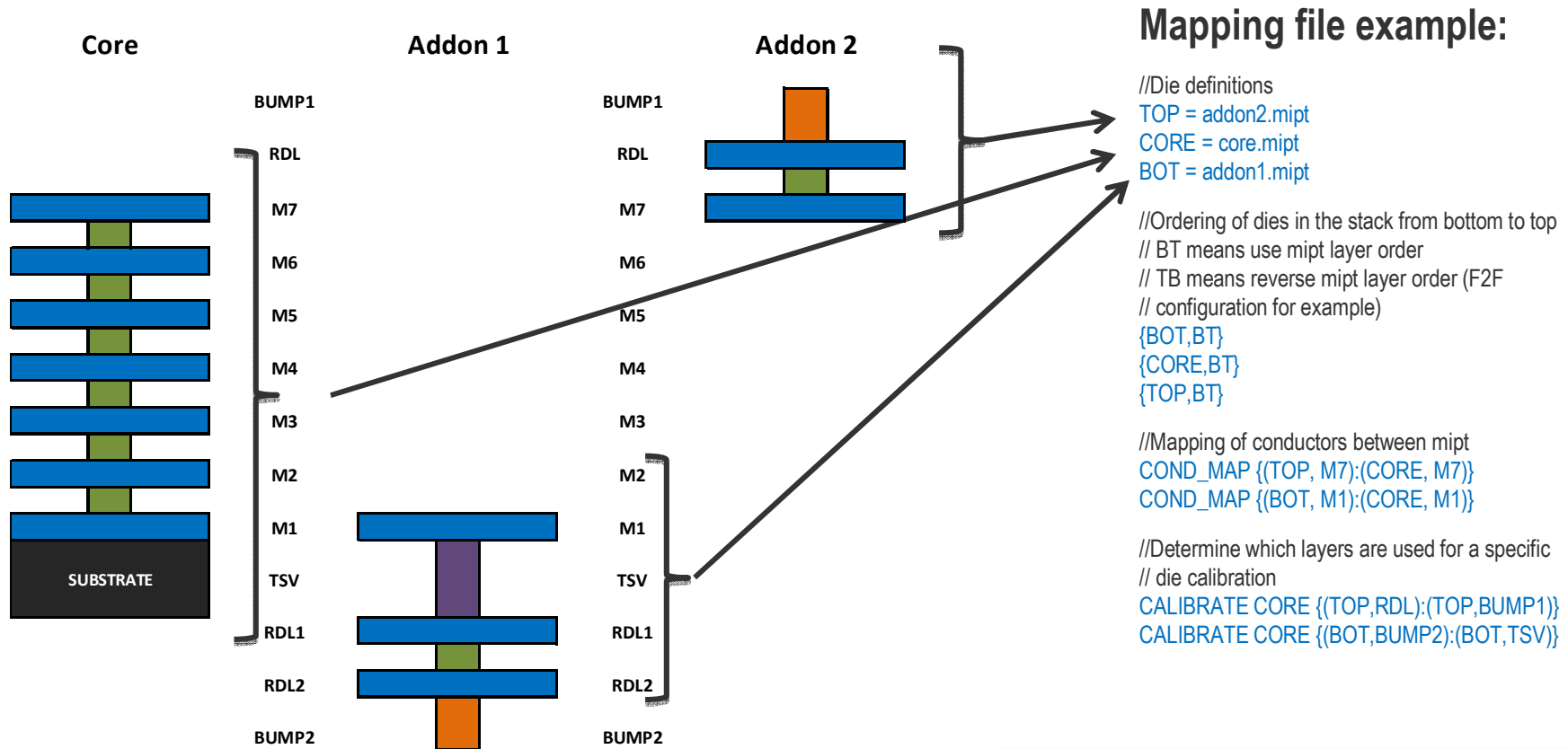
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- Extract the dies “in context”
- Do not netlist couplings; Fold them into top level capacitances
- Extract the package “in context” with the ground assumed at the board level
- Stitch the netlists



# Incremental calibration

- The same die can be put in different environments
- The extraction rules already exist for different metal stacks
- To avoid a need for creating new rule decks incremental calibration can be used



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